

Description

The DMG3401LSN uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

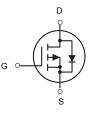
 V_{DS} = -30V, I_D = -6A R_{DS(ON)} <35m Ω @ V_{GS}=10V

Application

High power and current handing capability Lead free product is acquired Surface mount package PWM applications Load switch Power management







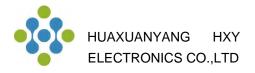
P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMG3401LSN	SOT-23	HXY MOSFET	3000

Absolute Maximum Ratings (T_A=25[°]C unless otherwise noted)

Symbol	Parameter	Limit	Unit
Vds	Drain-Source Voltage	-30	V
V _{GS}	Gate-Source Voltage	±20	V
lo	Drain Current-Continuous	-6	А
Ідм	Drain Current-Pulsed (Note 1)	-24	А
PD	Maximum Power Dissipation	1.32	W
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	125	°C <i>I</i> W



Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-30			V	
$\triangle BV_{DSS} / \triangle T$	BV _{DSS} Temperature Coefficient	Reference to $25^{\circ}C$, I _D =-1mA		-0.022		V/°C	
Basian	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-4A		28	35	m0	
Rds(on)		V _{GS} =-4.5V , I _D =-2A		40	55	mΩ	
V _{GS(th)}	Gate Threshold Voltage		-1.0		-2.5	V	
$ riangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	VGS-VDS, ID2500A		4.6		mV/°C	
l	Drain-Source Leakage Current	V _{DS} =-24V , V _{GS} =0V , T _J =25°C			1		
I _{DSS}		V _{DS} =-24V , V _{GS} =0V , T _J =55°C	5		uA		
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$			±100	nA	
gfs	Forward Transconductance	V _{DS} =-5V , I _D =-4A		15		S	
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		13		Ω	
Qg	Total Gate Charge (-4.5V)			9.7			
Qgs	Gate-Source Charge	V _{DS} =-15V , V _{GS} =-4.5V , I _D =-4A		2.5		nC	
Q_{gd}	Gate-Drain Charge			3			
T _{d(on)}	Turn-On Delay Time			16.4			
Tr	Rise Time V_{DD} =-15V , V_{GS} =-10V , R_G =3.3 Ω ,			20.2			
T _{d(off)}	Turn-Off Delay Time	I _D =-4A		55		ns	
T _f	Fall Time			10			
Ciss	Input Capacitance			750			
Coss	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz		150		pF	
Crss	rss Reverse Transfer Capacitance			127			
ls	Continuous Source Current ^{1,4}				-6.0	Α	
I _{SM}	Pulsed Source Current ^{2,4}	$V_G=V_D=0V$, Force Current			-24	А	
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25°C			-1.2	V	
trr	Reverse Recovery Time			18.3		nS	
Qrr	Reverse Recovery Charge	IF=-4A , dI/dt=100A/µs , Tյ=25℃		7.2		nC	

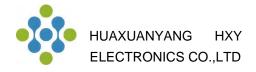
Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width $\leq 300 us$, duty cycle $\leq 2\%$ 3.The power dissipation is limited by 150°C $\,$ junction temperature

4. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics

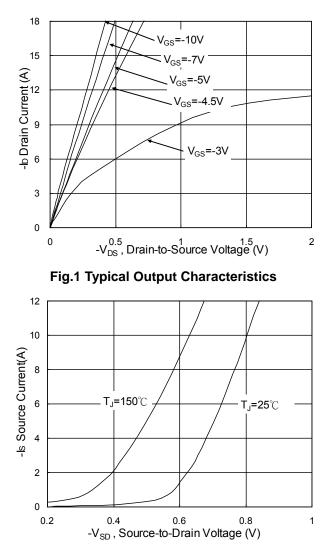


Fig.3 Forward Characteristics of Reverse

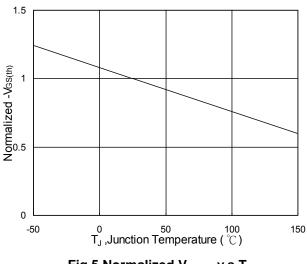


Fig.5 Normalized V_{GS(th)} v.s T_J

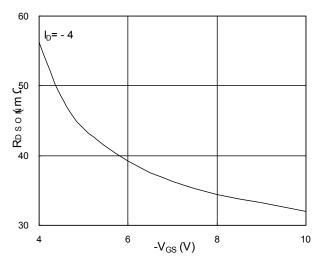


Fig.2 On-Resistance v.s Gate-Source

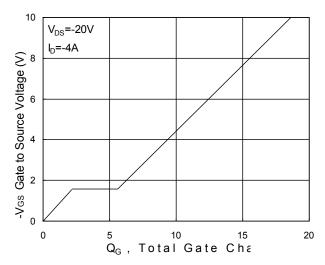


Fig.4 Gate-Charge Characteristics

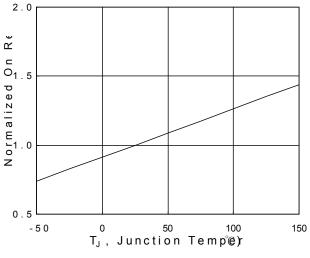
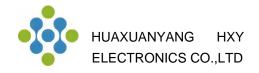


Fig.6 Normalized R_{DSON} v.s T_J



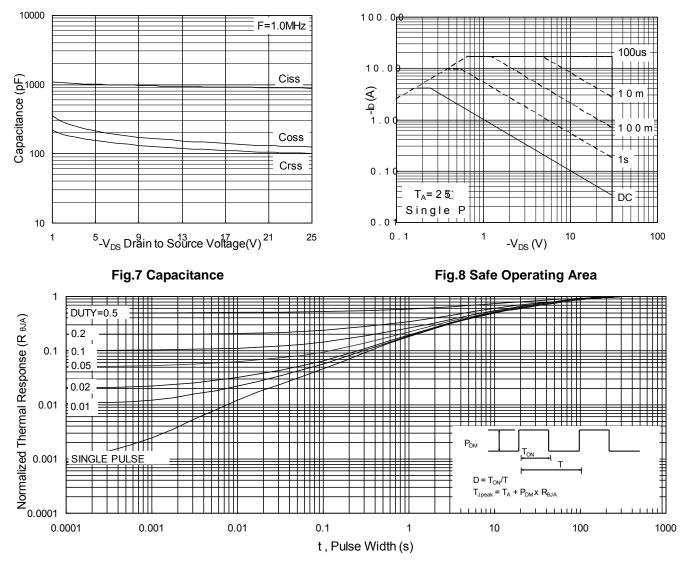


Fig.9 Normalized Maximum Transient Thermal Impedance

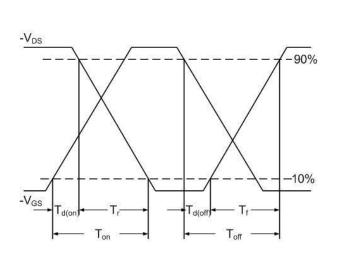


Fig.10 Switching Time Waveform

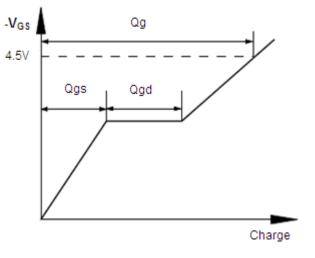
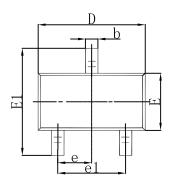
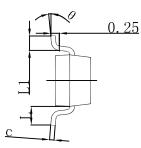


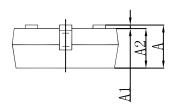
Fig.11 Gate Charge Waveform



SOT-23 Package Outline Dimensions

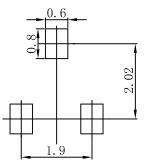






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	0.950 TYP 0.037 TYP		7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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